1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- · Start-Stop micro-hybrid applications
- · Transmission control
- Ultra high performance power switching



4. Quick reference data

Table 1. Quick reference data

rabio ii dai	ck reference data						
Symbol	Parameter	Conditions	ı	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	-	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	-	294	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10	(0.95	1.35	1.7	mΩ
Dynamic ch	naracteristics						,
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	-	10	25	nC
Source-drai	in diode						,
Q _r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; $Fig.~16$	-	-	25	-	nC
S	softness factor	$I_S = 25 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_i = 25 ^{\circ}\text{C}; \text{ Fig. 16}$	-	-	0.8	-	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	[d	G P
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK7Y1R7-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals; 4.9 mm x 4.45 mm x 1 mm body	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y1R7-40H	71H740

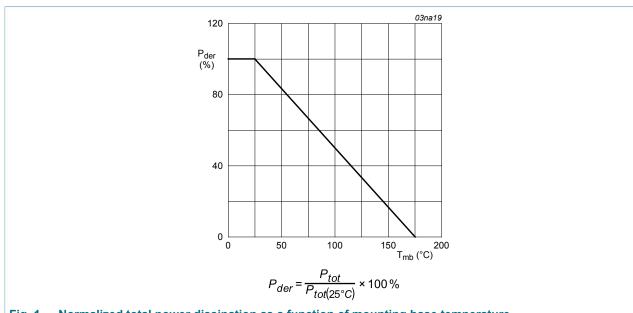
8. Limiting values

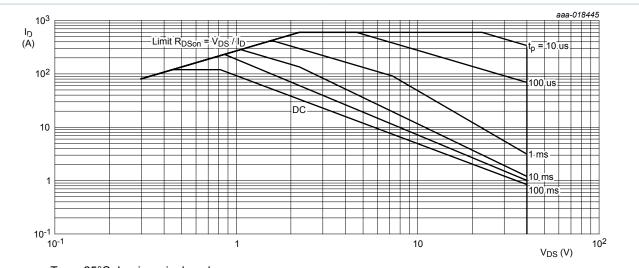
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	294	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C		-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 2		-	600	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	600	Α
Avalanche r	uggedness				,	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 120 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2] [3]	-	158	mJ

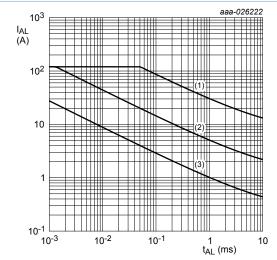
- [1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}$ C.
- [3] Refer to application note AN10273 for further information.





 T_{mb} = 25°C; I_{DM} is a single pulse

Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

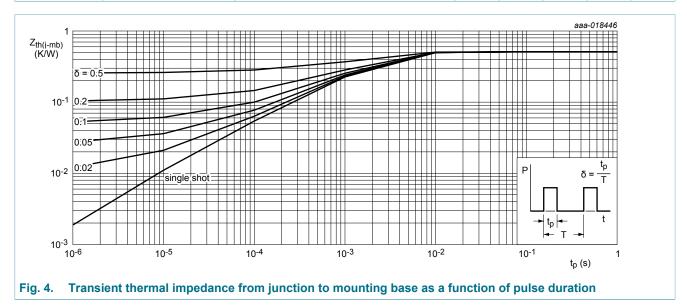
Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

N-channel 40 V, 1.7 m Ω standard level MOSFET in LFPAK56

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.39	0.51	K/W	



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; <u>Fig. 8</u> ; <u>Fig. 9</u>	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 8$	-	-	4.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; Fig. 8$	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.2	1	μΑ
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	1.8	10	μΑ
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	200	500	μΑ
I_{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10	0.95	1.35	1.7	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 105 °C; Fig. 11	1.34	2.05	2.7	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 125 °C; Fig. 11	1.48	2.24	3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11	1.86	2.78	3.7	mΩ
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	0.4	1.02	2.5	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	56	96	nC
Q_{GS}	gate-source charge	Fig. 12; Fig. 13	-	16	24	nC
Q_GD	gate-drain charge		-	10	25	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4095	6142	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	1083	1516	pF
C _{rss}	reverse transfer capacitance		-	178	393	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	14.6	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	12.6	-	ns
t _{d(off)}	turn-off delay time		-	35.2	-	ns
t _f	fall time		-	16.6		ns
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 15</u>	_	0.8	1.2	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; Fig. 16	-	32	-	ns
Q _r	recovered charge		-	25	-	nC
S	softness factor	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.8	-	
		I_S = 25 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 16	-	0.7	-	

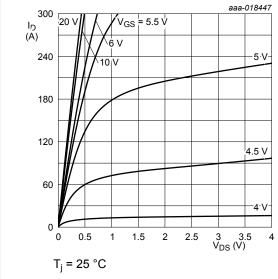


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

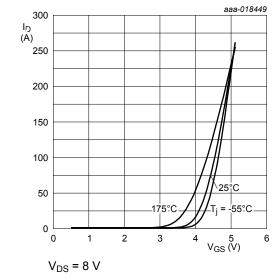


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

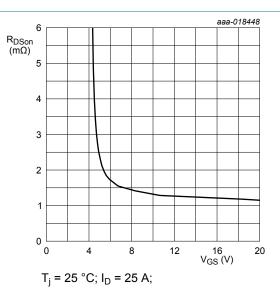
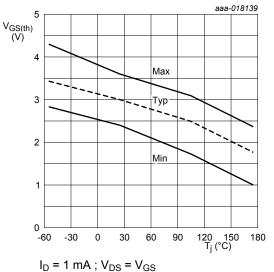


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



ID THINK, VDS VGS

Fig. 8. Gate-source threshold voltage as a function of junction temperature

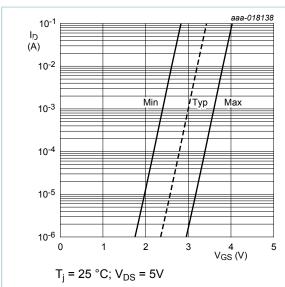


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

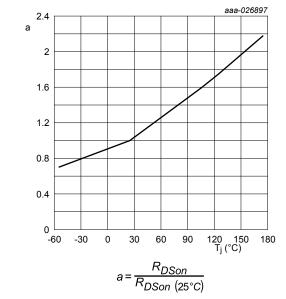


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

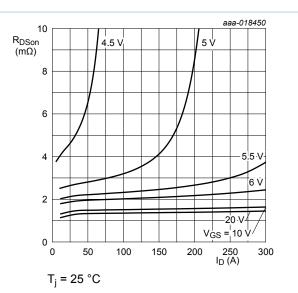


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

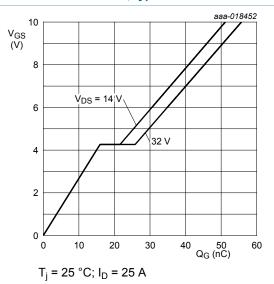


Fig. 12. Gate-source voltage as a function of gate charge; typical values

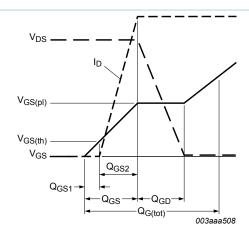
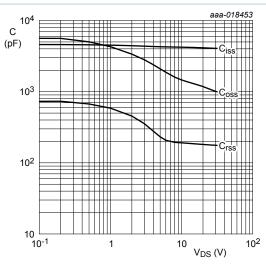


Fig. 13. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

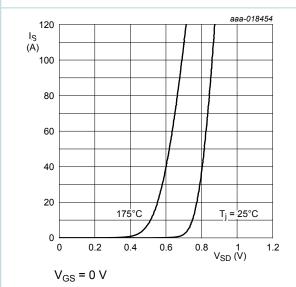
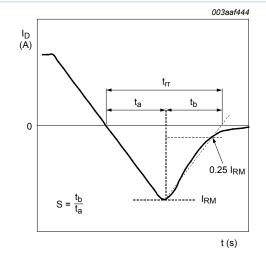


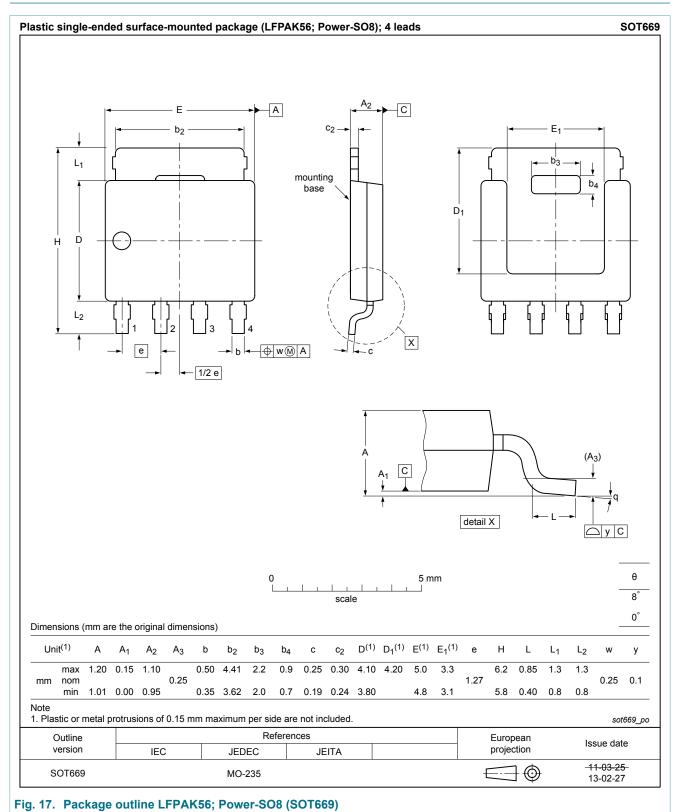
Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values



 $t_{rr} = t_a + t_b$

Fig. 16. Reverse recovery waveform definitions

11. Package outline



12. Legal information

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N-channel 40 V, 1.7 m Ω standard level MOSFET in LFPAK56

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